MC14518B, MC14520B

Dual Up Counters

The MC14518B dual BCD counter and the MC14520B dual binary counter are constructed with MOS P−channel and N−channel enhancement mode devices in a single monolithic structure. Each consists of two identical, independent, internally synchronous 4−stage counters. The counter stages are type D flip−flops, with interchangeable Clock and Enable lines for incrementing on either the positive−going or negative−going transition as required when cascading multiple stages. Each counter can be cleared by applying a high level on the Reset line. In addition, the MC14518B will count out of all undefined states within two clock periods. These complementary MOS up counters find primary use in multi−stage synchronous or ripple counting applications requiring low power dissipation and/or high noise immunity.

Features

- Diode Protection on All Inputs
- Supply Voltage Range = 3.0 Vdc to 18 Vdc
- Internally Synchronous for High Internal and External Speeds
- Logic Edge−Clocked Design — Incremented on Positive Transition of Clock or Negative Transition on Enable
- Capable of Driving Two Low−power TTL Loads or One Low−power Schottky TTL Load Over the Rated Temperature Range
- Pb−Free Packages are Available*

MAXIMUM RATINGS (Voltages Referenced to V_{SS}) (Note 1.)

Symbol	Parameter	Value	Unit
V_{DD}	DC Supply Voltage Range	−0.5 to +18.0	V
V_{in}, V_{out}	Input or Output Voltage Range (DC or Transient)	−0.5 to V_{DD} + 0.5	V
I_{in}, I_{out}	Input or Output Current (DC or Transient) per Pin	±10	mA
P_D	Power Dissipation, per Package (Note 2.)	500	mW
T_A	Operating Temperature Range	−55 to +125	°C
T_{stg}	Storage Temperature Range	−65 to +150	°C
T_L	Lead Temperature (8−Second Soldering)	260	°C

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

1. Maximum Ratings are those values beyond which damage to the device may occur.
2. Temperature Derating:
   Plastic “P and D/DW” Packages: – 7.0 mW/°C From 65°C To 125°C

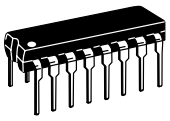
This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high−impedance circuit. For proper operation, V_{in} and V_{out} should be constrained to the range $V_{SS} \le (V_{in}$ or $V_{out}) \le V_{DD}$.

Unused inputs must always be tied to an appropriate logic voltage level (e.g., either V_{SS} or V_{DD}). Unused outputs must be left open.

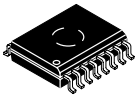
ON Semiconductor

http://onsemi.com

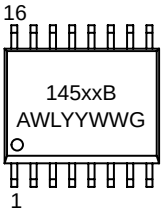
MARKING DIAGRAMS



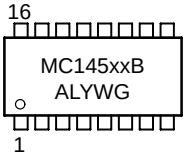
PDIP−16
P SUFFIX
CASE 648



SOIC−16
DW SUFFIX
CASE 751G



SOEIAJ−16
F SUFFIX
CASE 966

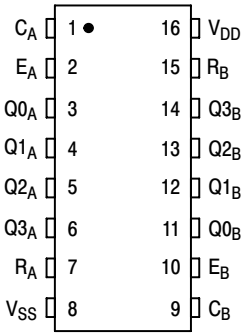


xx	= 18 or 20
A	= Assembly Location
WL, L	= Wafer Lot
YY, Y	= Year
WW, W	= Work Week
G	= Pb−Free Indicator

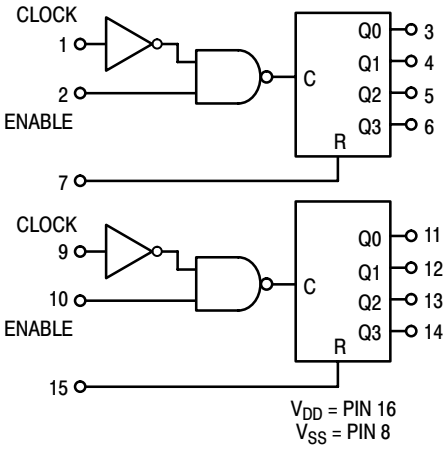
ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 7 of this data sheet.

PIN ASSIGNMENT



BLOCK DIAGRAM



TRUTH TABLE

Clock	Enable	Reset	Action
↗	1	0	Increment Counter
0	↘	0	Increment Counter
↘	X	0	No Change
X	↗	0	No Change
↗	0	0	No Change
1	↘	0	No Change
X	X	1	Q0 thru Q3 = 0

X = Don't Care

ELECTRICAL CHARACTERISTICS (Voltages Referenced to V_{SS})

Characteristic	Symbol	V_{DD} Vdc	− 55°C Min	− 55°C Max	25°C Min	25°C Typ (3.)	25°C Max	125°C Min	125°C Max	Unit
Output Voltage “0” Level V_{in} = V_{DD} or 0	V_{OL}	5.0 10 15	— — —	0.05 0.05 0.05	— — —	0 0 0	0.05 0.05 0.05	— — —	0.05 0.05 0.05	Vdc
“1” Level V_{in} = 0 or V_{DD}	V_{OH}	5.0 10 15	4.95 9.95 14.95	— — —	4.95 9.95 14.95	5.0 10 15	— — —	4.95 9.95 14.95	— — —	Vdc
Input Voltage “0” Level (V_O = 4.5 or 0.5 Vdc) (V_O = 9.0 or 1.0 Vdc) (V_O = 13.5 or 1.5 Vdc)	V_{IL}	5.0 10 15	— — —	1.5 3.0 4.0	— — —	2.25 4.50 6.75	1.5 3.0 4.0	— — —	1.5 3.0 4.0	Vdc
“1” Level (V_O = 0.5 or 4.5 Vdc) (V_O = 1.0 or 9.0 Vdc) (V_O = 1.5 or 13.5 Vdc)	V_{IH}	5.0 10 15	3.5 7.0 11	— — —	3.5 7.0 11	2.75 5.50 8.25	— — —	3.5 7.0 11	— — —	Vdc
Output Drive Current (V_{OH} = 2.5 Vdc) Source (V_{OH} = 4.6 Vdc) (V_{OH} = 9.5 Vdc) (V_{OH} = 13.5 Vdc)	I_{OH}	5.0 5.0 10 15	– 3.0 – 0.64 – 1.6 – 4.2	— — — —	– 2.4 – 0.51 – 1.3 – 3.4	– 4.2 – 0.88 – 2.25 – 8.8	— — — —	– 1.7 – 0.36 – 0.9 – 2.4	— — — —	mAdc
(V_{OL} = 0.4 Vdc) Sink (V_{OL} = 0.5 Vdc) (V_{OL} = 1.5 Vdc)	I_{OL}	5.0 10 15	0.64 1.6 4.2	— — —	0.51 1.3 3.4	0.88 2.25 8.8	— — —	0.36 0.9 2.4	— — —	mAdc
Input Current	I_{in}	15	—	± 0.1	—	±0.00001	± 0.1	—	± 1.0	µAdc
Input Capacitance (V_{in} = 0)	C_{in}	—	—	—	—	5.0	7.5	—	—	pF
Quiescent Current (Per Package)	I_{DD}	5.0 10 15	— — —	5.0 10 20	— — —	0.005 0.010 0.015	5.0 10 20	— — —	150 300 600	µAdc
Total Supply Current (4.) (5.) (Dynamic plus Quiescent, Per Package) (C_L = 50 pF on all outputs, all buffers switching)	I_T	5.0 10 15	I_T = (0.6 µA/kHz) f + I_{DD} I_T = (1.2 µA/kHz) f + I_{DD} I_T = (1.7 µA/kHz) f + I_{DD}							µAdc

3. Data labelled “Typ” is not to be used for design purposes but is intended as an indication of the IC’s potential performance.
4. The formulas given are for the typical characteristics only at 25°C.
5. To calculate total supply current at loads other than 50 pF:

$$I_T(C_L) = I_T(50\ pF) + (C_L - 50)\ Vfk$$

where: I_T is in µA (per package), C_L in pF, V = (V_{DD} – V_{SS}) in volts, f in kHz is input frequency, and k = 0.002.

SWITCHING CHARACTERISTICS [6.] (C_L = 50 pF, T_A = 25°C)

Characteristic	Symbol	V_{DD}	All Types			Unit
			Min	Typ [7.]	Max	
Output Rise and Fall Time	t_{TLH},					ns
t_{TLH}, t_{THL} = (1.5 ns/pF) C_L + 25 ns	t_{THL}	5.0	—	100	200	
t_{TLH}, t_{THL} = (0.75 ns/pF) C_L + 12.5 ns		10	—	50	100	
t_{TLH}, t_{THL} = (0.55 ns/pF) C_L + 9.5 ns		15	—	40	80	
Propagation Delay Time	t_{PLH},					ns
Clock to Q/Enable to Q	t_{PHL}					
t_{PLH}, t_{PHL} = (1.7 ns/pF) C_L + 215 ns		5.0	—	280	560	
t_{PLH}, t_{PHL} = (0.66 ns/pF) C_L + 97 ns		10	—	115	230	
t_{PLH}, t_{PHL} = (0.5 ns/pF) C_L + 75 ns		15	—	80	160	
Reset to Q	t_{PHL}					ns
t_{PHL} = (1.7 ns/pF) C_L + 265 ns		5.0	—	330	650	
t_{PHL} = (0.66 ns/pF) C_L + 117 ns		10	—	130	230	
t_{PHL} = (0.66 ns/pF) C_L + 95 ns		15	—	90	170	
Clock Pulse Width	$t_{w(H)}$	5.0	200	100	—	ns
	$t_{w(L)}$	10	100	50	—	
		15	70	35	—	
Clock Pulse Frequency	f_{cl}	5.0	—	2.5	1.5	MHz
		10	—	6.0	3.0	
		15	—	8.0	4.0	
Clock or Enable Rise and Fall Time	t_{THL}, t_{TLH}	5.0	—	—	15	μs
		10	—	—	5	
		15	—	—	4	
Enable Pulse Width	$t_{WH(E)}$	5.0	440	220	—	ns
		10	200	100	—	
		15	140	70	—	
Reset Pulse Width	$t_{WH(R)}$	5.0	280	125	—	ns
		10	120	55	—	
		15	90	40	—	
Reset Removal Time	t_{rem}	5.0	– 5	– 45	—	ns
		10	15	– 15	—	
		15	20	– 5	—	

6. The formulas given are for the typical characteristics only at 25°C.
7. Data labelled “Typ” is not to be used for design purposes but is intended as an indication of the IC’s potential performance.

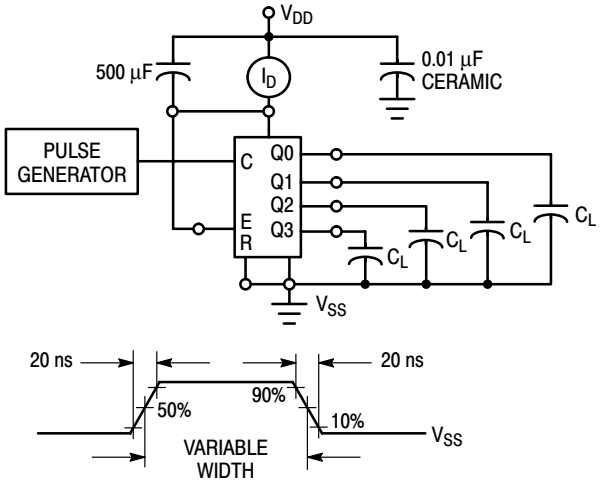


Figure 1. Power Dissipation Test Circuit and Waveform

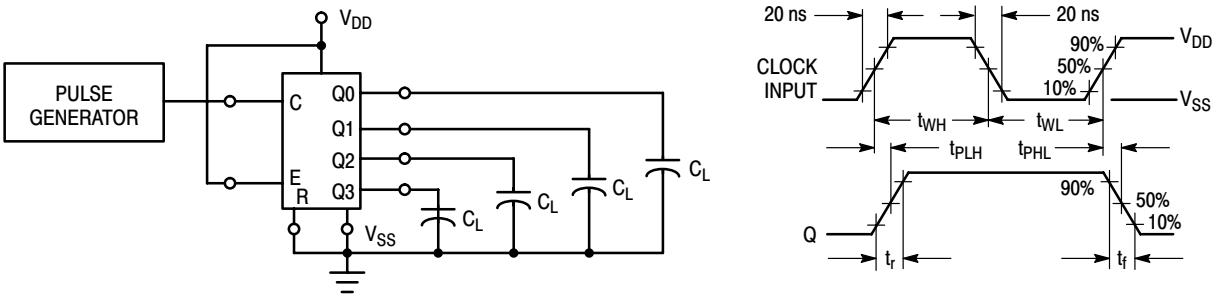


Figure 2. Switching Time Test Circuit and Waveforms

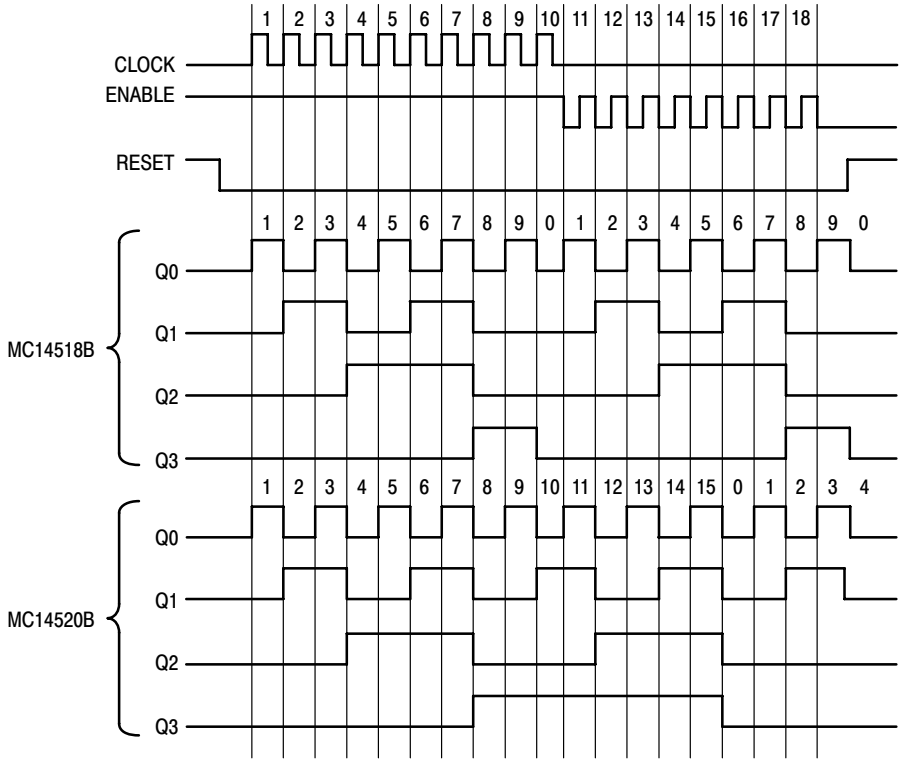


Figure 3. Timing Diagram

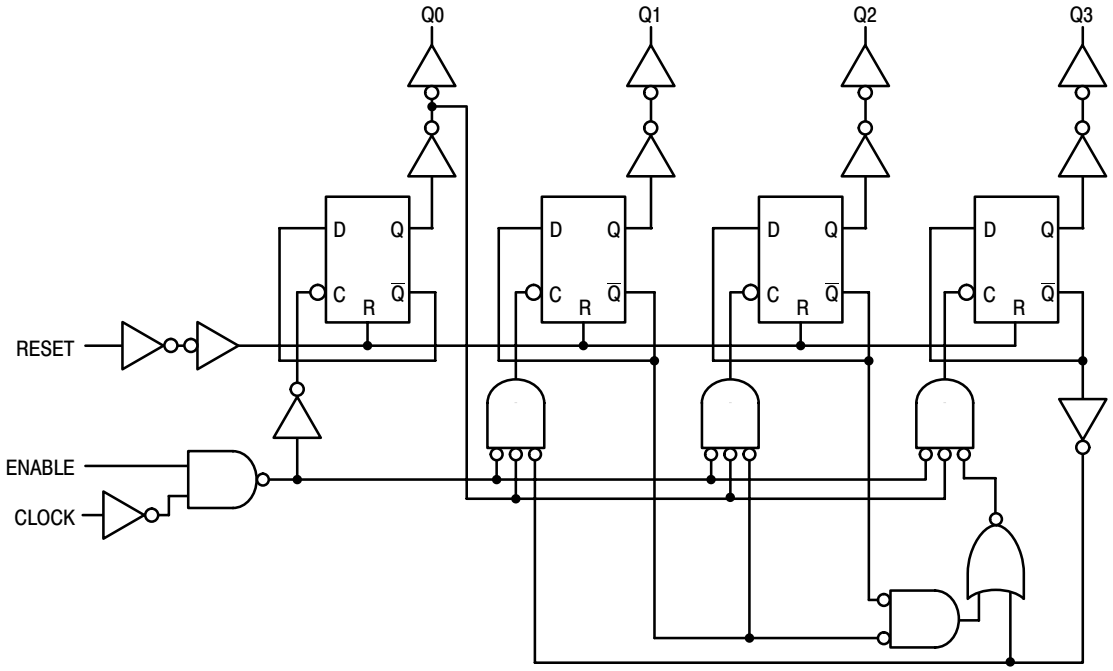


Figure 4. Decade Counter (MC14518B) Logic Diagram
(1/2 of Device Shown)

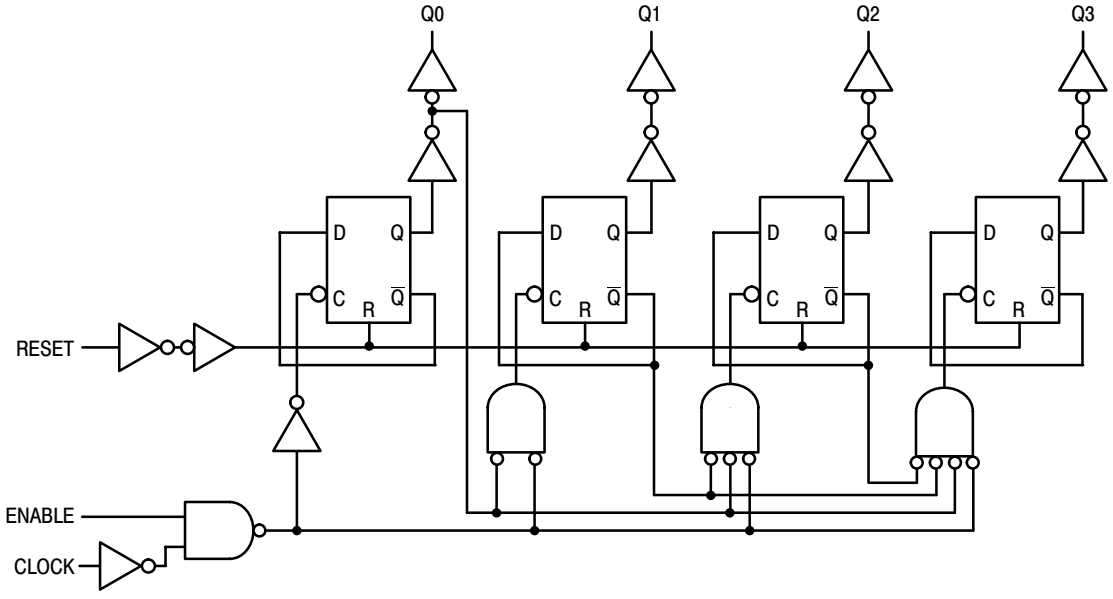


Figure 5. Binary Counter (MC14520B) Logic Diagram
(1/2 of Device Shown)

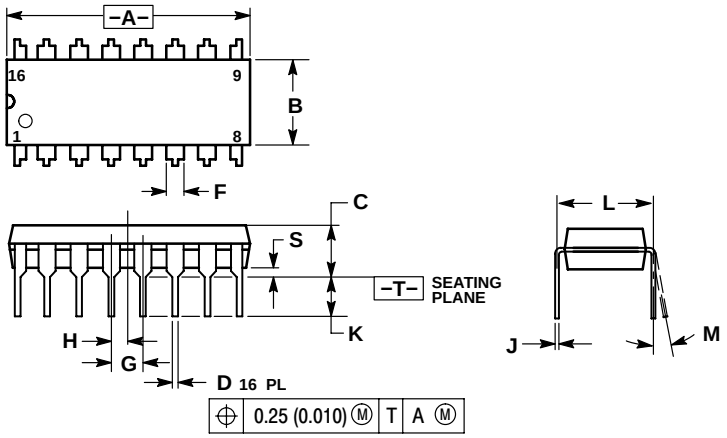
ORDERING INFORMATION

Device	Package	Shipping†
MC14518BCP	PDIP−16	500 Units / Rail
MC14518BCPG	PDIP−16 (Pb−Free)	500 Units / Rail
MC14518BDW	SOIC−16	47 Units / Rail
MC14518BDWG	SOIC−16 (Pb−Free)	47 Units / Rail
MC14518BDWR2	SOIC−16	1000 Units / Tape & Reel
MC14518BDWR2G	SOIC−16 (Pb−Free)	1000 Units / Tape & Reel
MC14518BFEL	SOEIAJ−16	2000 Units / Tape & Reel
MC14518BFELG	SOEIAJ−16 (Pb−Free)	2000 Units / Tape & Reel
MC14520BCP	PDIP−16	500 Units / Rail
MC14520BCPG	PDIP−16 (Pb−Free)	500 Units / Rail
MC14520BDW	SOIC−16	47 Units / Rail
MC14520BDWG	SOIC−16 (Pb−Free)	47 Units / Rail
MC14520BDWR2	SOIC−16	1000 Units / Tape & Reel
MC14520BDWR2G	SOIC−16 (Pb−Free)	1000 Units / Tape & Reel
MC14520BFEL	SOEIAJ−16	2000 Units / Tape & Reel
MC14520BFELG	SOEIAJ−16 (Pb−Free)	2000 Units / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

PACKAGE DIMENSIONS

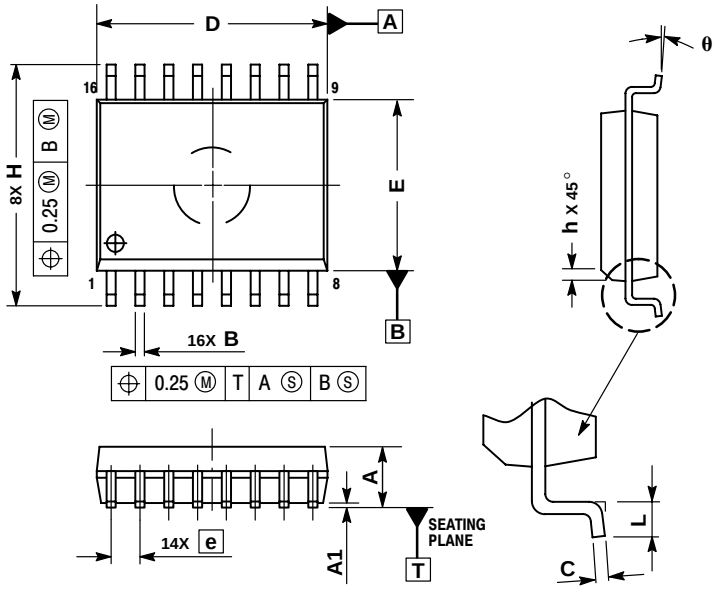
PDIP−16
P SUFFIX
PLASTIC DIP PACKAGE
CASE 648−08
ISSUE T



NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. DIMENSION L TO CENTER OF LEADS WHEN FORMED PARALLEL.
4. DIMENSION B DOES NOT INCLUDE MOLD FLASH.
5. ROUNDED CORNERS OPTIONAL.

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
A	0.740	0.770	18.80	19.55
B	0.250	0.270	6.35	6.85
C	0.145	0.175	3.69	4.44
D	0.015	0.021	0.39	0.53
F	0.040	0.70	1.02	1.77
G	0.100 BSC		2.54 BSC	
H	0.050 BSC		1.27 BSC	
J	0.008	0.015	0.21	0.38
K	0.110	0.130	2.80	3.30
L	0.295	0.305	7.50	7.74
M	0 °	10 °	0 °	10 °
S	0.020	0.040	0.51	1.01

SOIC−16
DW SUFFIX
PLASTIC SOIC PACKAGE
CASE 751G−03
ISSUE C

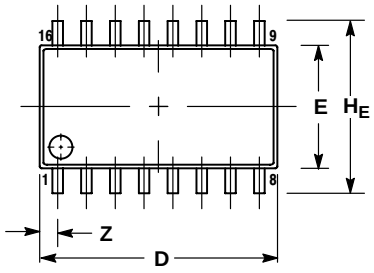


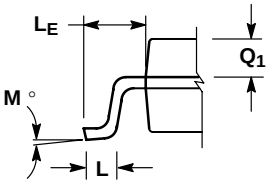
NOTES:
1. DIMENSIONS ARE IN MILLIMETERS.
2. INTERPRET DIMENSIONS AND TOLERANCES PER ASME Y14.5M, 1994.
3. DIMENSIONS D AND E DO NOT INLCUDE MOLD PROTRUSION.
4. MAXIMUM MOLD PROTRUSION 0.15 PER SIDE.
5. DIMENSION B DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.13 TOTAL IN EXCESS OF THE B DIMENSION AT MAXIMUM MATERIAL CONDITION.

	MILLIMETERS	
DIM	MIN	MAX
A	2.35	2.65
A1	0.10	0.25
B	0.35	0.49
C	0.23	0.32
D	10.15	10.45
E	7.40	7.60
e	1.27 BSC	
H	10.05	10.55
h	0.25	0.75
L	0.50	0.90
θ	0 °	7 °

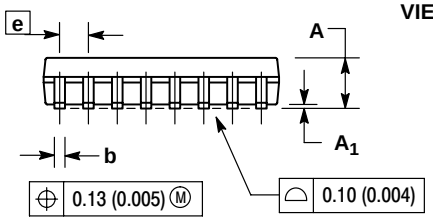
PACKAGE DIMENSIONS

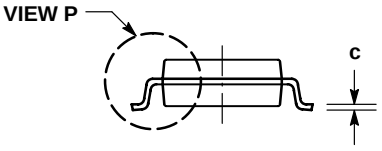
SOEIAJ−16
F SUFFIX
PLASTIC EIAJ SOIC PACKAGE
CASE 966−01
ISSUE O





DETAIL P





NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH OR PROTRUSIONS AND ARE MEASURED AT THE PARTING LINE. MOLD FLASH OR PROTRUSIONS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
4. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
5. THE LEAD WIDTH DIMENSION (b) DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE LEAD WIDTH DIMENSION AT MAXIMUM MATERIAL CONDITION. DAMBAR CANNOT BE LOCATED ON THE LOWER RADIUS OR THE FOOT. MINIMUM SPACE BETWEEN PROTRUSIONS AND ADJACENT LEAD TO BE 0.46 (0.018).

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
A	---	2.05	---	0.081
A_1	0.05	0.20	0.002	0.008
b	0.35	0.50	0.014	0.020
c	0.18	0.27	0.007	0.011
D	9.90	10.50	0.390	0.413
E	5.10	5.45	0.201	0.215
e	1.27 BSC		0.050 BSC	
H_E	7.40	8.20	0.291	0.323
L	0.50	0.85	0.020	0.033
L_E	1.10	1.50	0.043	0.059
M	0 °	10 °	0 °	10 °
Q_1	0.70	0.90	0.028	0.035
Z	---	0.78	---	0.031

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:
Literature Distribution Center for ON Semiconductor
P.O. Box 61312, Phoenix, Arizona 85082−1312 USA
Phone: 480−829−7710 or 800−344−3860 Toll Free USA/Canada
Fax: 480−829−7709 or 800−344−3867 Toll Free USA/Canada
Email: orderlit@onsemi.com

N. American Technical Support: 800−282−9855 Toll Free USA/Canada

Japan: ON Semiconductor, Japan Customer Focus Center
2−9−1 Kamimeguro, Meguro−ku, Tokyo, Japan 153−0051
Phone: 81−3−5773−3850

ON Semiconductor Website: http://onsemi.com

Order Literature: http://www.onsemi.com/litorder

For additional information, please contact your local Sales Representative.

MC14518B/D